



DISCRETE POWER DIODES and THYRISTORS
DATA BOOK



181RKI SERIES

PHASE CONTROL THYRISTORS

Stud Version

Features

- Hermetic glass-metal seal
- $dv/dt = 1000V/\mu s$ option
- International standard case TO-209AB (TO-93)
- Threaded studs UNF 3/4 - 16UNF2A

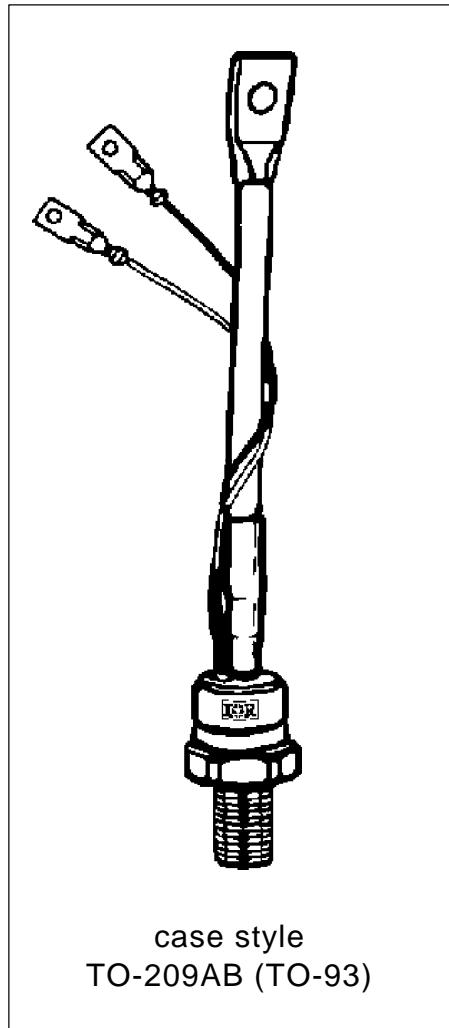
180A

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	181RKI	Units
$I_{T(AV)}$	180	A
@ T_c	80	$^{\circ}\text{C}$
$I_{T(RMS)}$	285	A
I_{TSM}	3800	A
@ 60Hz	4000	A
I^2t	72	KA^2s
@ 60Hz	66	KA^2s
V_{DRM}/V_{RRM}	400 to 1000	V
t_q typical	100	μs
T_J	- 40 to 125	$^{\circ}\text{C}$



181RKI Series

ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA
181RKI	40	400	500	30
	80	800	900	
	100	1000	1100	

On-state Conduction

Parameter	181RKI	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Case temperature	180	A	180° conduction, half sine wave
	80	°C	
$I_{T(RMS)}$ Max. RMS on-state current	285	A	DC @ 79°C case temperature
I_{TSM} Max. peak, one-cycle non-repetitive surge current	3800		Sinusoidal half wave, Initial $T_J = T_J$ max.
	4000		
	3500		
	3660		
I^2t Maximum I^2t for fusing	72	KA ² s	No voltage reapplied
	66		
	61		
	56		
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	720	KA ² \sqrt{s}	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.83	V	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	0.89		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	0.92	mΩ	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
r_{t2} High level value of on-state slope resistance	0.81		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
V_{TM} Max. on-state voltage	1.35	V	$I_{pk} = 570A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		

Switching

Parameter	181RKI	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	300	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.0	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ C$
	100		

181RKI Series

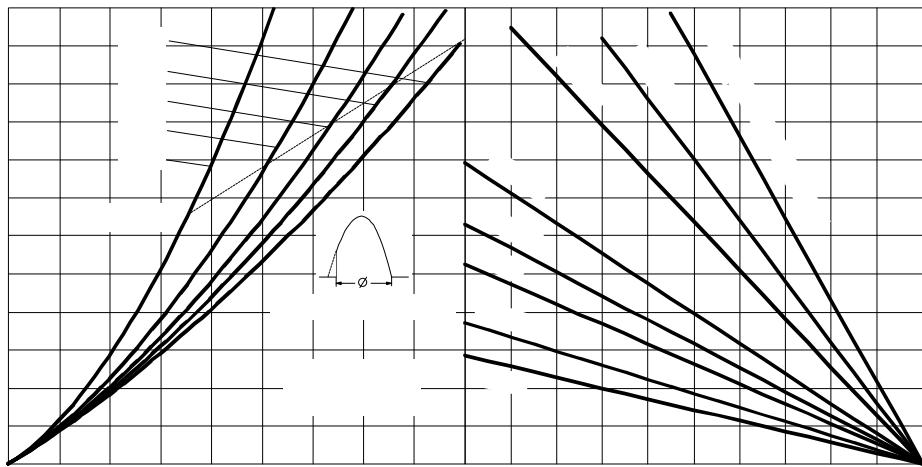


Fig. 3 - On-state Power Loss Characteristics

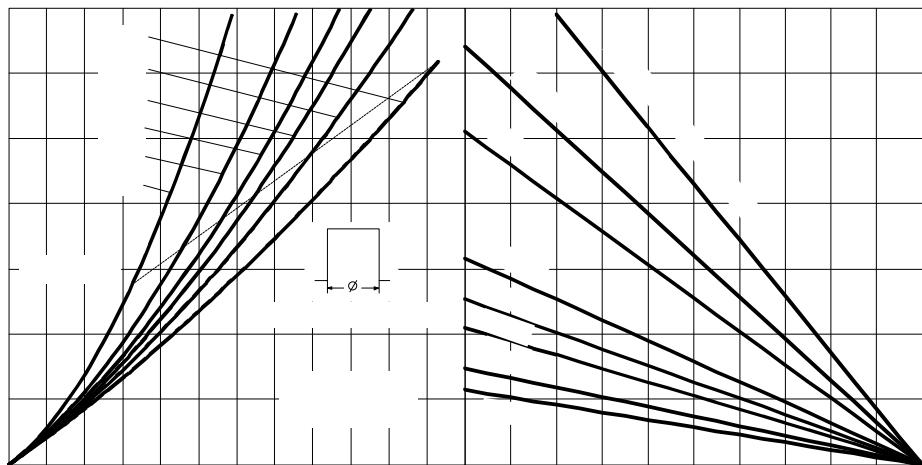


Fig. 4 - On-state Power Loss Characteristics

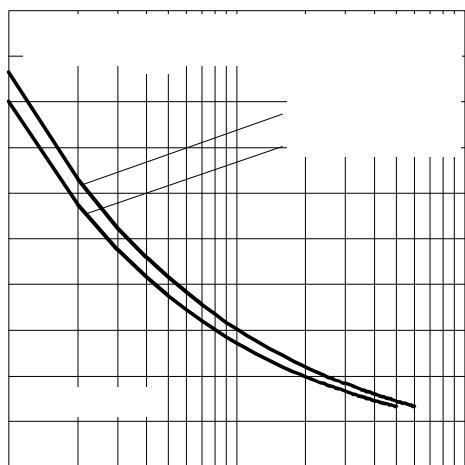


Fig. 5 - Maximum Non-Repetitive Surge Current

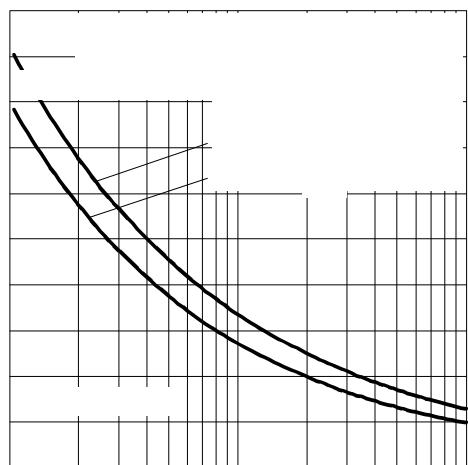


Fig. 6 - Maximum Non-Repetitive Surge Current

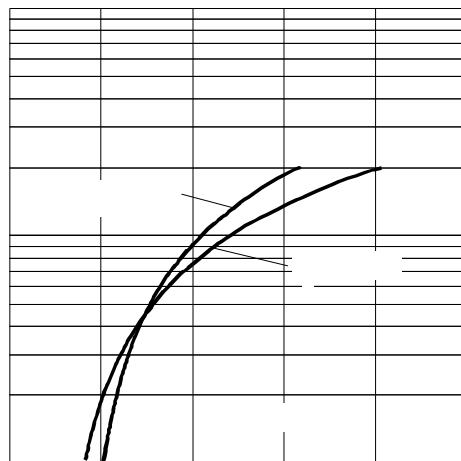


Fig. 7 - On-state Voltage Drop Characteristics

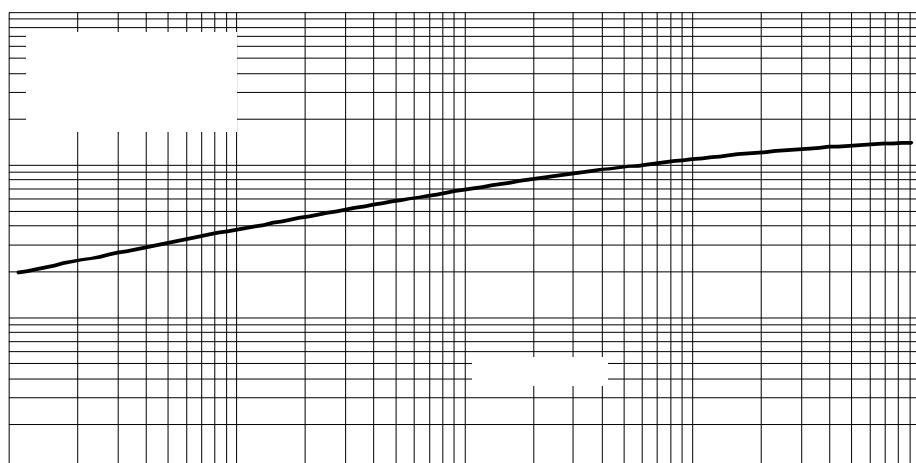


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

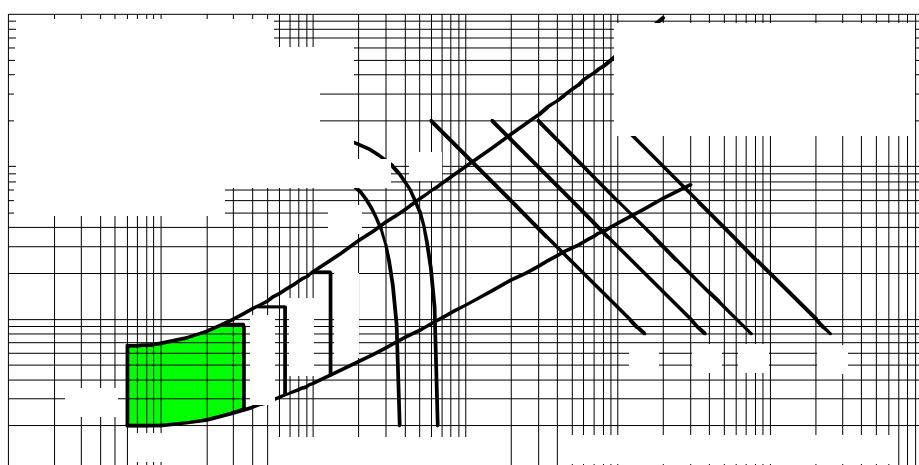


Fig. 9 - Gate Characteristics

Blocking

Parameter	181RKi	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	30	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter	181RKi		Units	Conditions	
P_{GM} Maximum peak gate power	10		W	$T_J = T_J$ max, $t_p \leq 5\text{ms}$	
$P_{G(AV)}$ Maximum average gate power				$T_J = T_J$ max, $f = 50\text{Hz}$, $d\% = 50$	
I_{GM} Max. peak positive gate current	3.0		A	$T_J = T_J$ max, $t_p \leq 5\text{ms}$	
+ V_{GM} Maximum peak positive gate voltage	20		V	$T_J = T_J$ max., $t_p \leq 5\text{ms}$	
- V_{GM} Maximum peak negative gate voltage	5.0				
I_{GT} DC gate current required to trigger	TYP.	MAX.	mA	$T_J = -40^\circ\text{C}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
	130	-			
	65	150			
	35	-			
V_{GT} DC gate voltage required to trigger	2.0	-	V	$T_J = -40^\circ\text{C}$	
	1.2	2.5		$T_J = 25^\circ\text{C}$	
	0.9	-		$T_J = 125^\circ\text{C}$	
I_{GD} DC gate current not to trigger	10		mA	Max. gate current/ voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied	
V_{GD} DC gate voltage not to trigger	0.25		V		

Thermal and Mechanical Specification

Parameter	181RKi	Units	Conditions
T_J Max. operating temperature range	-40 to 125	°C	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJC} Max. thermal resistance, junction to case	0.15	K/W	DC operation
R_{thCS} Max. thermal resistance, case to heatsink	0.04		Mounting surface, smooth, flat and greased
T Mounting torque, ± 10%	31 (275)	Nm (lbf-in)	Non lubricated threads
	24.5 (210)		Lubricated threads
wt Approximate weight	280	g	
Case style	TO - 209AB (TO-93)	See Outline Table	

181RKI Series

ΔR_{thJC} Conduction

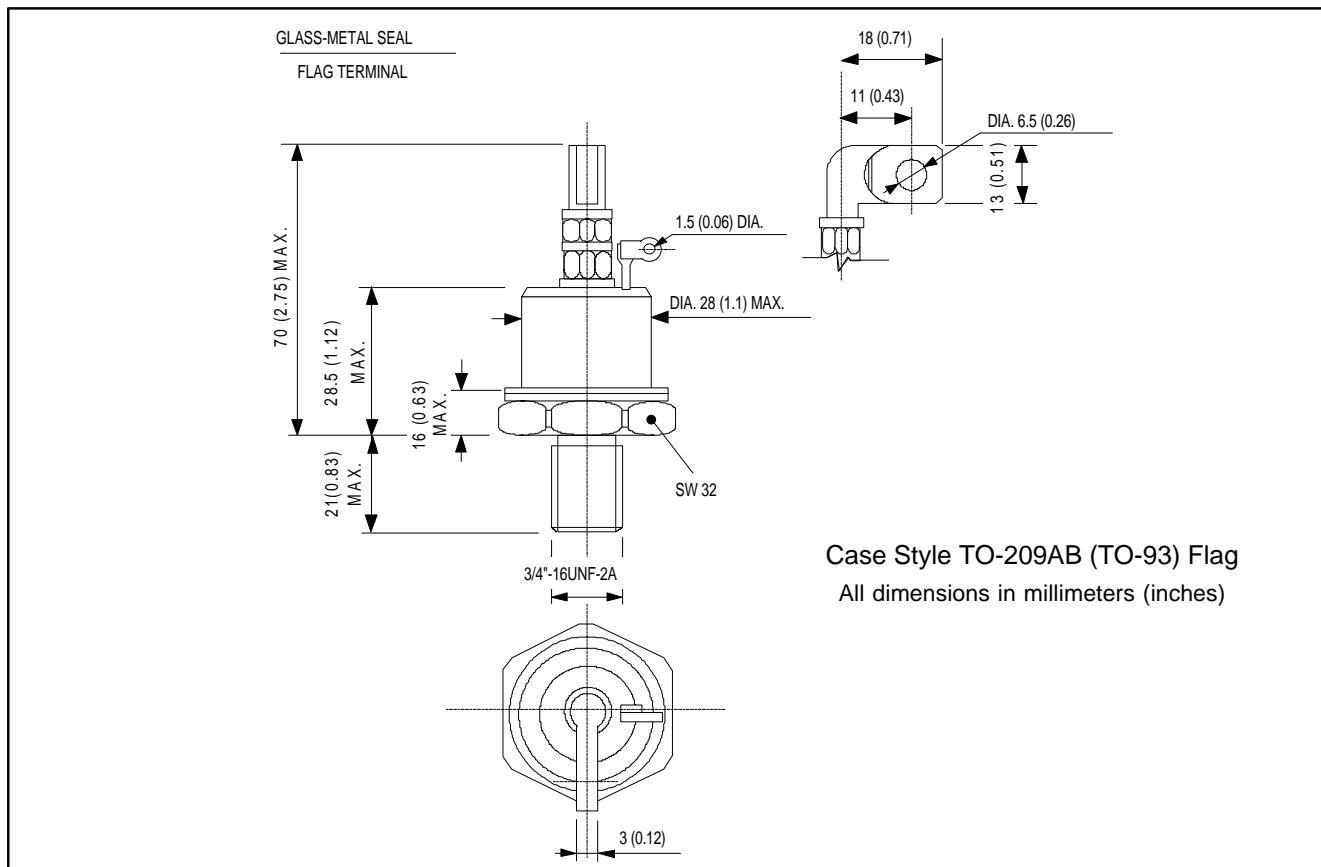
(The following table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.050	0.032	K/W	$T_J = T_{J \text{ max.}}$
120°	0.063	0.059		
90°	0.080	0.082		
60°	0.118	0.124		
30°	0.225	0.228		

Ordering Information Table

Device Code		18	1	RKI	100		
		1	2	3	4	5	6
1	- $I_{(AV)}$ rated average output current (rounded/10)						
2	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Leads) 1 = Fast - on terminals (Gate and Auxiliary Cathode Leads) 2 = Flag terminals (For Cathode and Gate Terminals)						
3	- Thyristor						
4	- Voltage code: Code x 10 = V_{RRM} (See Voltage Rating Table)						
5	- None = Stud base UNF 3/4 - 16UNF threads						
6	- Critical dv/dt: None = 500V/ μ sec S90 = 1000V/ μ sec						

Outline Table



Outline Table

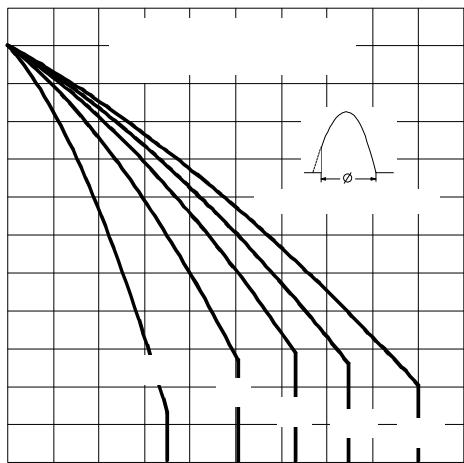
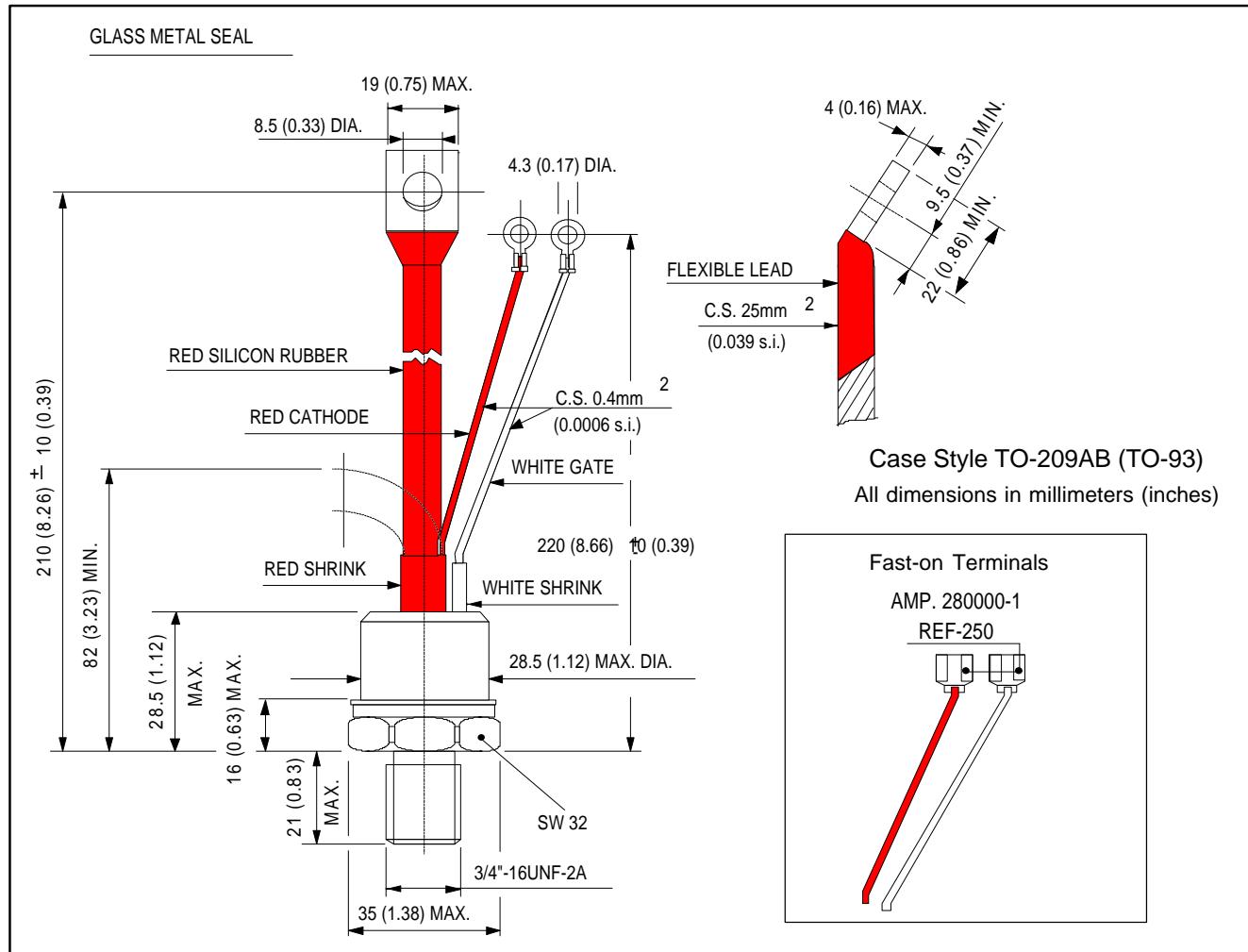


Fig. 1 - Current Ratings Characteristics

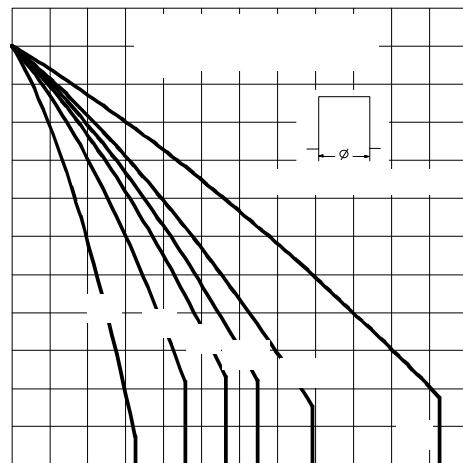


Fig. 2 - Current Ratings Characteristics